

**TWO-STEP SOURCE SIDE IMPLANT FOR IMPROVING SOURCE
RESISTANCE AND SHORT CHANNEL EFFECT IN DEEP SUB-0.18 μ m FLASH
MEMORY TECHNOLOGY**

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ABSTRACT

10 Methods of forming flash memory EEPROM devices having lightly doped source
region near the critical gate region and a heavily doped source region away from the
critical gate region. In a first embodiment a first source mask is formed exposing source
regions and portions of the gates and implanting n dopant ions, replacing the first source
mask with a second source mask that exposes a portion of the source regions and
implanting n⁺ dopant ions. In a second embodiment a source mask is formed exposing a
15 portion of the source regions and implanting n⁺ dopant ions.

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